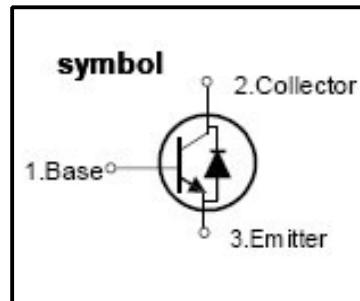
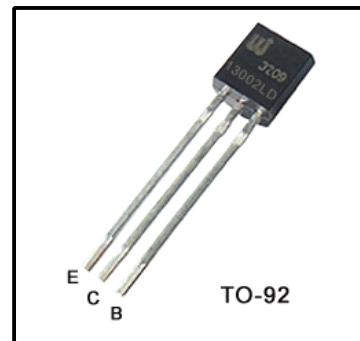


*High Voltage Fast -Switching NPN Power Transistor*
**Features**

- Very High Switching Speed
- High Voltage Capability
- Wide Reverse Bias SOA


**General Description**

This Device is designed for high voltage , High speed Switching characteristics required such as lighting system, switching mode power supply.


**Absolute Maximum Ratings**

Symbol	Parameter	Test Conditions	Value	Units
$V_{CES}$	Collector-Emitter Voltage	$V_{BE}=0$	350	V
$V_{CEO}$	Collector-Emitter Voltage	$I_B=0$	200	V
$V_{EBO}$	Emitter-Base Voltage	$I_C=0$	7	V
$I_C$	Collector Current		1.5	A
$I_{CP}$	Collector pulse Current		3.0	A
$I_B$	Base Current		1	A
$I_{BM}$	Base Peak Current	$t_P=5\text{ms}$	2	A
$P_c$	Total Dissipation at $T_c=25^\circ\text{C}$		1	W
$T_J$	Operation Junction temperature		-40~150	°C
$T_{STG}$	Storage Temperature		-40~150	°C

Tc:Case temperature(good cooling)

**Thermal Characteristics**

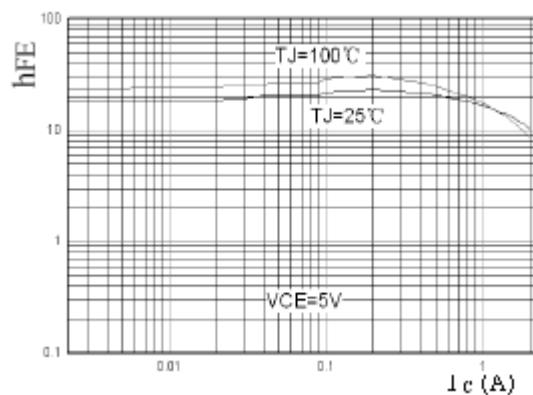
Symbol	Parameter	value	Units
$R_{QJA}$	Thermal Resistance Junction to Ambient (Max)	125	°C/W

**Electrical Characteristics**( $T_c=25^\circ\text{C}$  unless otherwise noted)

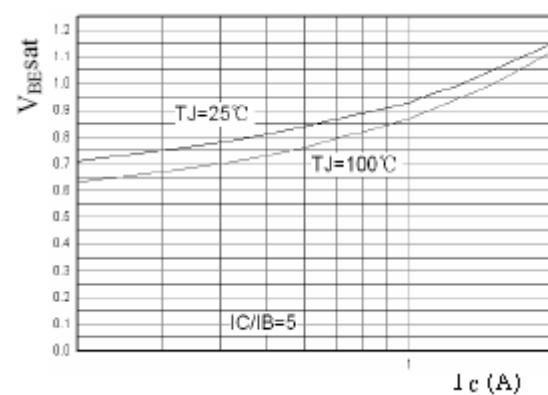
Symbol	Parameter	Test Conditions	Value			Units
			Min	Typ	Max	
$V_{CEO(sus)}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}, I_B=0$	200	-	-	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=0.5\text{A}, I_B=0.1\text{A}$ $I_C=1.0\text{A}, I_B=0.25\text{A}$	-	-	1.0 1.5	V
$V_{BE(sat)}$	Base -Emitter Saturation voltage	$I_C=0.5\text{A}, I_B=0.1\text{A}$ $I_C=1.0\text{A}, I_B=0.25\text{A}$	-	-	1.0 1.5	V
$I_{CBO}$	Collector- Base Cutoff Current	$V_{CB}=350\text{V}, I_E=0$	-	-	100	$\mu\text{A}$
$I_{CEO}$	Collector- Emitter Cutoff Current	$V_{CE}=200\text{V}, I_B=0$	-	-	50	$\mu\text{A}$
$I_{EBO}$	Emitter- Base Cutoff Current	$V_{EB}=7\text{V}, I_C=0$	-	-	10	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$V_{CE}=5\text{V}, I_C=0.2\text{A}$	8	-	50	
		$V_{CE}=5\text{V}, I_C=1.0\text{A}$	5	-	-	
$t_s$ $t_f$	Storage Time Fall Time	$V_{CC}=24\text{V}, I_C=0.5\text{A}$ $I_{B1}=-I_{B2}=0.1\text{A}$	-	1.8 0.21	4.0 0.5	$\mu\text{s}$
		$V_{CE}=10\text{V}, I_C=0.5\text{A}$	4	-	-	MHz

Note:

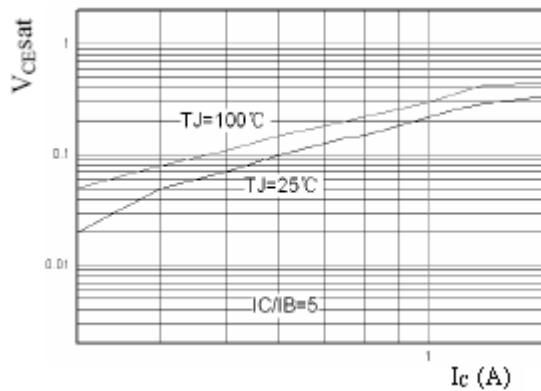
Pulse Test : Pulse width 300,Duty cycle 2%



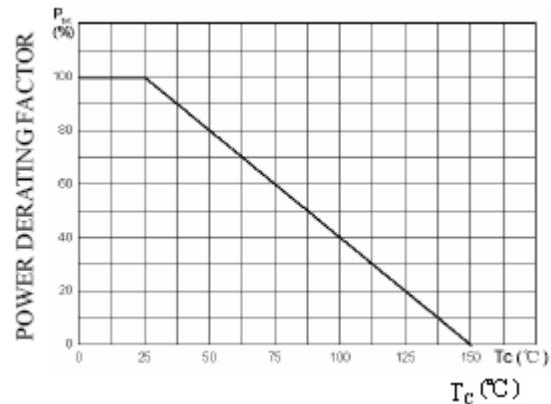
**Fig.1 DC Current Gain**



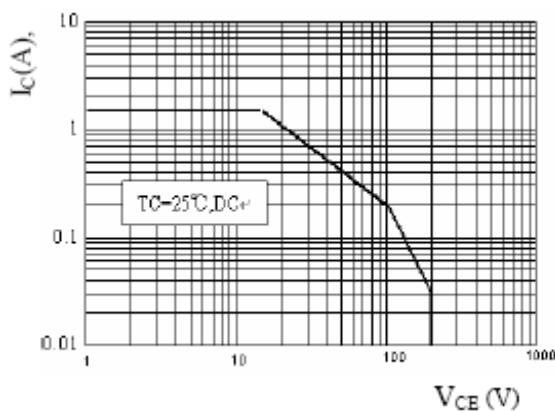
**Fig.2 Base -Emitter Saturation Voltage**



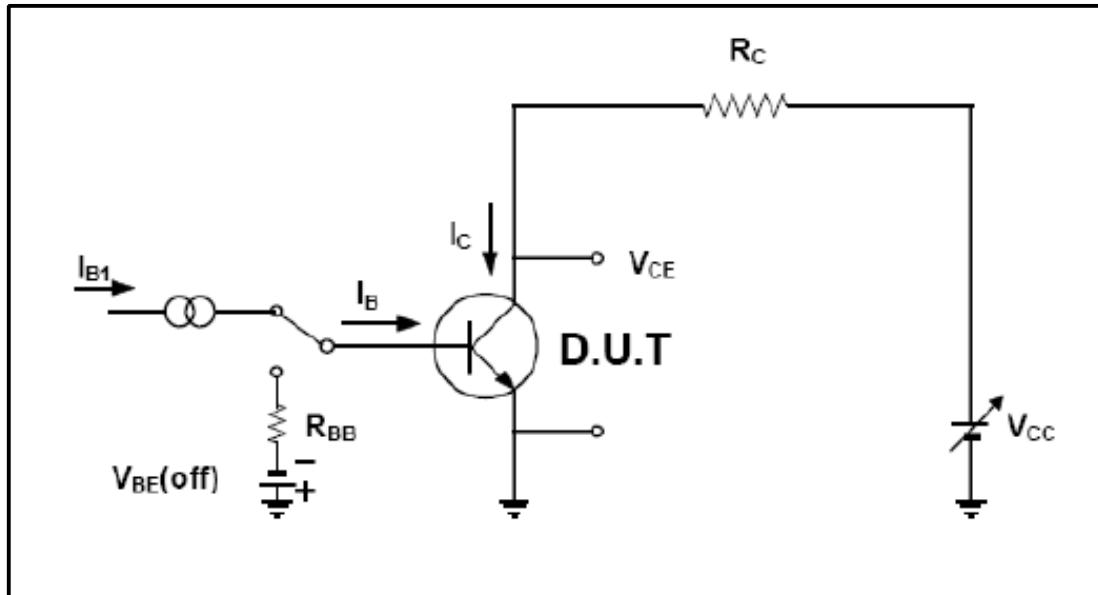
**Fig.3 Collector-Emitter Saturation Voltage**



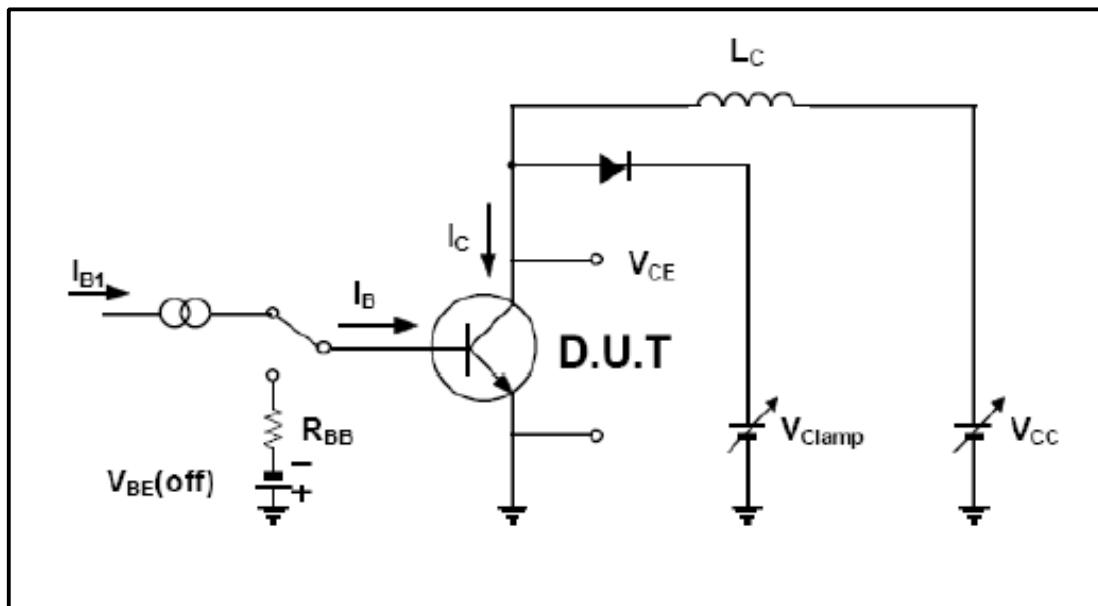
**Fig.6 Power Derating**



**Fig.5 Static Characteristics**



**Resistive Load Switching Test Circuit**



**Inductive Load Switching & RBSOA Test Circuit**

**To-92 Package Dimension**

**Unit:mm**

